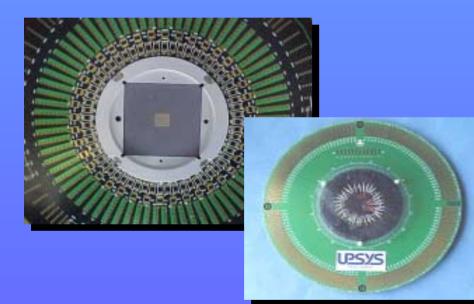
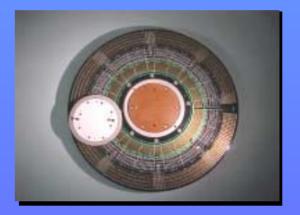


Improvements in Vertical Probing



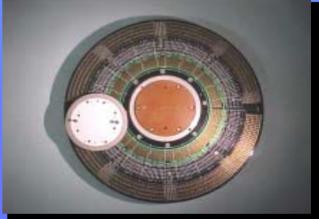




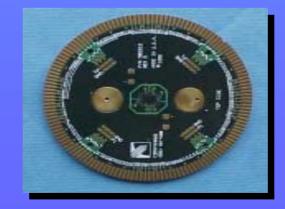
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Isabelle George and Jean Michel Jurine Upsys Probe Technology 283 Bld John Kennedy 91100 Corbeil Essonnes FRANCE



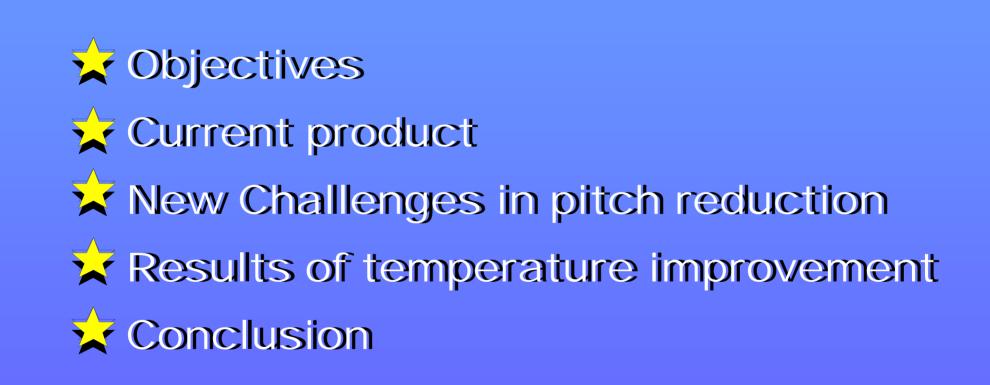




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Outline





Main Parameters to be improved







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Customers Needs

Requirements	1999	2000	2001	2002
Pad Pitch (μm)	100	70	50	45
Bump Pitch (μm)	225	178	150	127
Temperature (°C)	25 to 150	-40 to 200	-40 to 200	-40 to 200

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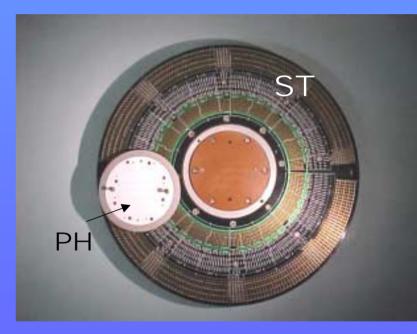


Current Product

Pitch:

5 mils probes 4 mils Probes 3 mils probes

down to 225 µm down to 175 µm down to 135 µm down to 105 µm



Temperature : Amb and HT (up to 150°C)

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Pitch Reduction

New challenges for vertical probing

Sub-100 µm Pitch

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One step down to 95 µm

Enhancement of current cobra

- Same grid material
- Drilling techniques:
 - laser ablation
- Space transformer:

 hand wire , MLC with organic thin film, micro PCB

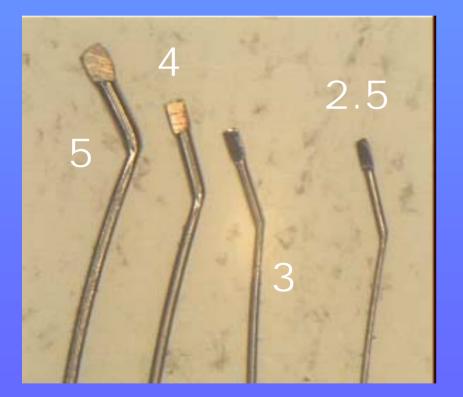
• Main Change:

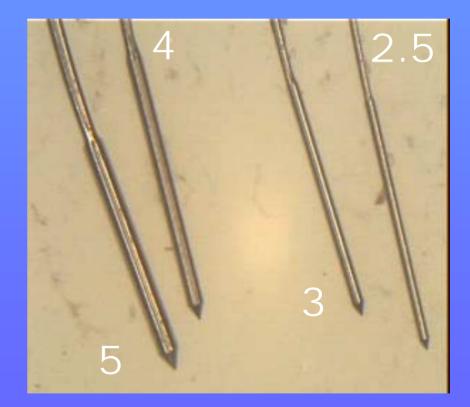
– probe diameter 2.5 mills

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Probe Diameters (mils) Head





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From 95 µm to 70 µm

Enhancement of current cobra

- Same grid material
- Same drilling techniques:
 - laser ablation
- Main changes:
 - space transformer based on Si interface
 - probe diameter down to 1 mils

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New Vertical Technology*

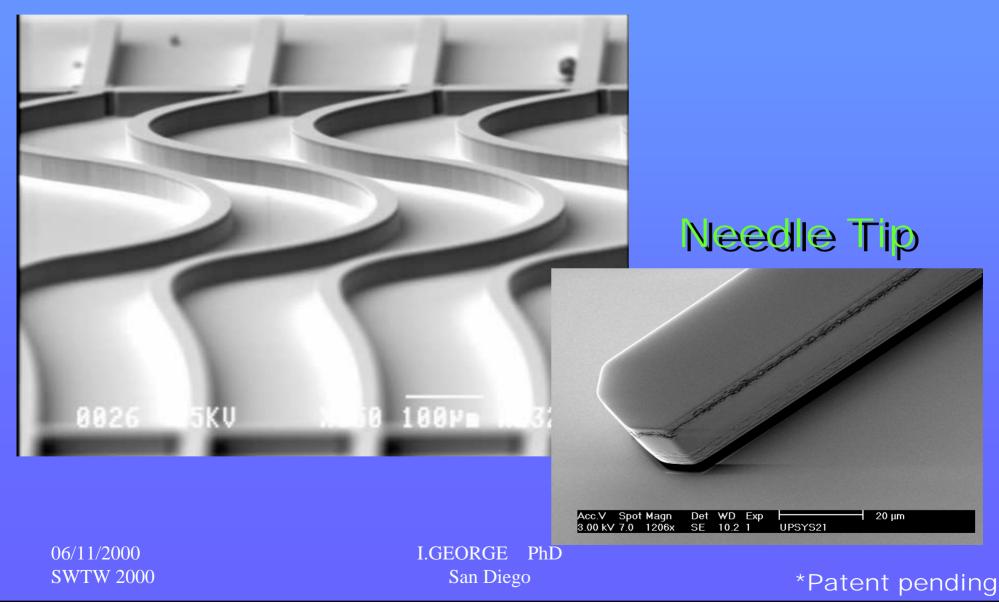
• New material:

- Silicon for: probe, grid and ST interface
- New technology:
 - DRIE + metallization

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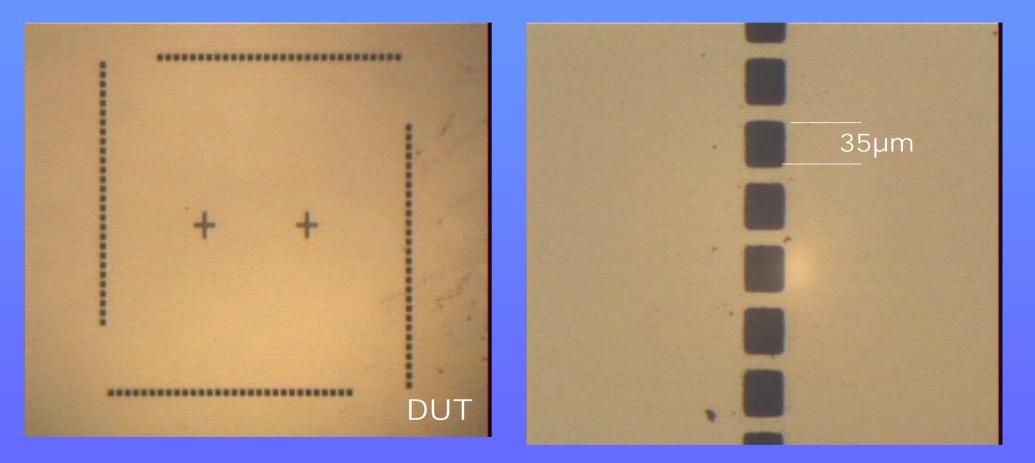


Needle Shape * (SEM)





Silicon Grid*



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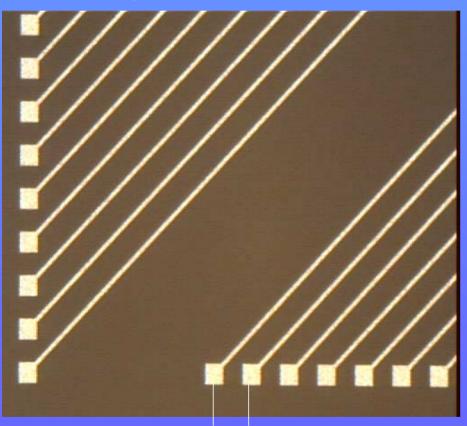
I.GEORGE PhD San Diego

* Patent pending

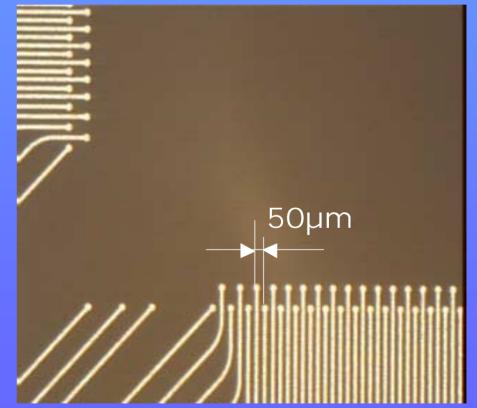


Silicon ST *

External pad



Chip layout



125µm

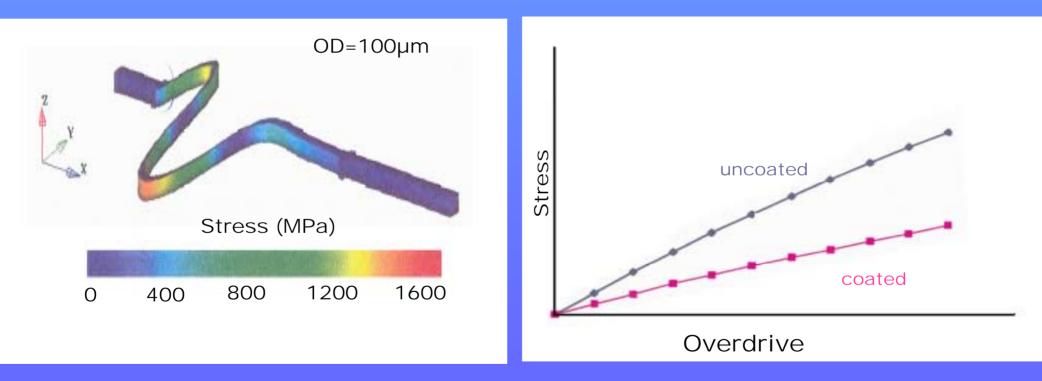
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* Patent pending



Stress versus overdrive

MemCad

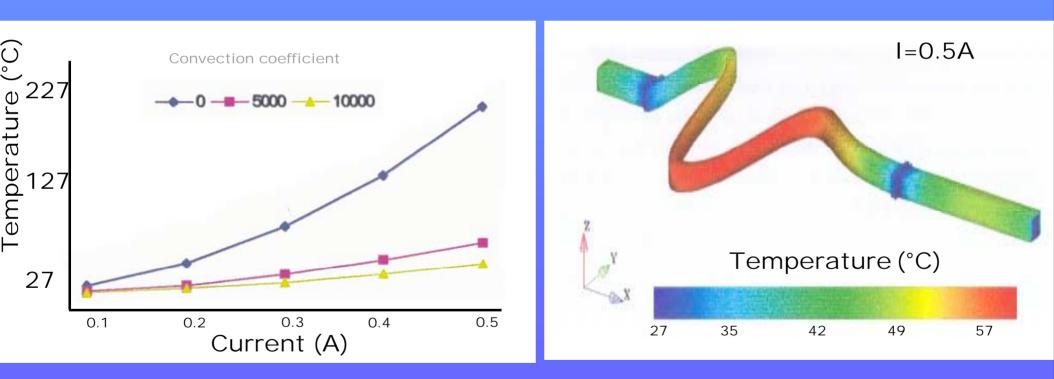


Fracture stress of Si=7GPa

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Temperature versus current



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Overdrive versus force

160 160 4 140 140 Ovrdrive (µm) 120 120 **Overdrive (hm)** 100 100 80 80 60 **60 40 40** 20 20 0 0 1,5 0,5 2 2,5 0 1 3 3,5 0,01 0,02 0,03 0,04 0.05 0,06 0,07 0 Maximum Stress (GPa) Force (N)

Non linear FEA: Nastran

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Expected Performance:

- I = 0.4 A
- R < 1 Ohm
- Impact size = $15X30 \,\mu m^2$
- Force = 1 to 1.5 g/mils
- Planarity = 1 mils



Temperature improvement

New challenge for vertical probing

-40°C up to 200°C

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Current Technology

Elevated temperature probe card utilized since 97:

HT material (Head and ST)
HT curing process of ST with a specific resin
Control of the padding position
« Control of the planarity »

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Market needs -40°C to 200°C

Automotive





Smart cards

Mobile phones

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2 different probe cards to address
 -40°C and 200°C

- Test hardware achieved
 - 40°C: demonstrated in a static way and need to be fully evaluated in test environment
- 200°C : extrapolation of current probe card

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Conclusion

Vertical probing solutions will satisfy pitch reduction and temperature new requirement

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